

Min Sup Choi

List of Publications by Year in descending order

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22
papers

3,699
citations

471509

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6153
citing authors

#	ARTICLE	IF	CITATIONS
1	Anomalous persistent p-type behavior of WSe ₂ field-effect transistors by oxidized edge-induced Fermi-level pinning. <i>Journal of Materials Chemistry C</i> , 2022, 10, 846-853.	5.5	5
2	Fermi Level Pinning Dependent 2D Semiconductor Devices: Challenges and Prospects. <i>Advanced Materials</i> , 2022, 34, e2108425.	21.0	80
3	Low-Resistance p-Type Ohmic Contacts to Ultrathin WSe ₂ by Using a Monolayer Dopant. <i>ACS Applied Electronic Materials</i> , 2021, 3, 2941-2947.	4.3	14
4	Chemical Dopant-Free Doping by Annealing and Electron Beam Irradiation on 2D Materials. <i>Advanced Electronic Materials</i> , 2021, 7, 2100449.	5.1	14
5	Analytical measurements of contact resistivity in two-dimensional WSe ₂ field-effect transistors. <i>2D Materials</i> , 2021, 8, 045019.	4.4	9
6	Damage-Free Atomic Layer Etch of WSe ₂ : A Platform for Fabricating Clean Two-Dimensional Devices. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 1930-1942.	8.0	24
7	Electrical characterization of 2D materials-based field-effect transistors. <i>2D Materials</i> , 2021, 8, 012002.	4.4	111
8	High carrier mobility in graphene doped using a monolayer of tungsten oxyselenide. <i>Nature Electronics</i> , 2021, 4, 731-739.	26.0	41
9	Transferred via contacts as a platform for ideal two-dimensional transistors. <i>Nature Electronics</i> , 2019, 2, 187-194.	26.0	172
10	Homogeneous molybdenum disulfide tunnel diode formed <i>via</i> chemical doping. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	15
11	Fermi Level Pinning at Electrical Metal Contacts of Monolayer Molybdenum Dichalcogenides. <i>ACS Nano</i> , 2017, 11, 1588-1596.	14.6	618
12	High Electric Field Carrier Transport and Power Dissipation in Multilayer Black Phosphorus Field Effect Transistor with Dielectric Engineering. <i>Advanced Functional Materials</i> , 2017, 27, 1604025.	14.9	47
13	Electrically Driven Reversible Phase Changes in Layered In ₂ Se ₃ Crystalline Film. <i>Advanced Materials</i> , 2017, 29, 1703568.	21.0	77
14	Effects of plasma treatment on surface properties of ultrathin layered MoS ₂ . <i>2D Materials</i> , 2016, 3, 035002.	4.4	59
15	Passivated ambipolar black phosphorus transistors. <i>Nanoscale</i> , 2016, 8, 12773-12779.	5.6	77
16	Carrier transport at the metal-MoS ₂ interface. <i>Nanoscale</i> , 2015, 7, 9222-9228.	5.6	99
17	High performance vertical tunneling diodes using graphene/hexagonal boron nitride/graphene hetero-structure. <i>Applied Physics Letters</i> , 2014, 104, 053103.	3.3	35
18	Lateral MoS ₂ p-n Junction Formed by Chemical Doping for Use in High-Performance Optoelectronics. <i>ACS Nano</i> , 2014, 8, 9332-9340.	14.6	507

#	ARTICLE	IF	CITATIONS
19	Metal-Semiconductor Barrier Modulation for High Photoresponse in Transition Metal Dichalcogenide Field Effect Transistors. Scientific Reports, 2014, 4, 4041.	3.3	99
20	Flexible and Transparent MoS ₂ Field-Effect Transistors on Hexagonal Boron Nitride-Graphene Heterostructures. ACS Nano, 2013, 7, 7931-7936.	14.6	947
21	Controlled charge trapping by molybdenum disulphide and graphene in ultrathin heterostructured memory devices. Nature Communications, 2013, 4, 1624.	12.8	595
22	Plasma treatments to improve metal contacts in graphene field effect transistor. Journal of Applied Physics, 2011, 110, .	2.5	53